# First measurements on apsel5T\_TC

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SuperB



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1

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# Apsel5T\_TC

TSV

- With more than 1 year delay, Tezzaron/Chartered delivered the first chips of the pilot run, in the 2D Intertier version (300 um-thick "analog" tier)
- The PA output pads of the 3D-desi structures in the 2D wafers were
  metalized (i.e. bondable):
  - A partial (i.e. only the analog part of the centric test has been possible, so far ...
- Goals: test the matrices to characterize the new V.I. technology:
  - compare the FE performances to what expected from design (noise, Gain, G-dispersion, ...)

2nd Wafer

1<sup>st</sup> wafer

# Apsel5T\_TC:

• The charge-collecting electrode is implemented by a deep-N-well extended over the 40um cell

• The M2 matrix differs from M1 in using enclosed layout transistors as input devices of the analog FE more robust against rad. damage (expected no difference in performance@0 dose)



- Shaper-less output and  $V_{\rm fbk}$  may be tuned to modify the PA output



### Analog FE

#### Main design features and simulation results

- W/L=30/0.3
- I<sub>D</sub>=20 μA, power dissipation=35 μW
- C<sub>D</sub>=250 fF
- 🛚 ~1 μs peaking time
- Charge sensitivity (G<sub>Q</sub>): 750 mV/fC
- Equivalent noise charge (ENC): 33 e-
- Threshold dispersion (∆Q<sub>t</sub>): 40 e-(34 e- from the SFE, 22 e- from the discriminator)





L. Ratti, "DNW CMOS MAPS and hybrid pixels in3D technology", SuperB Workshop IX

SuperB Workshop IX

### The "first" (Chip 1) Fe55 Spectrum





2Gaussian FIT:  $\mu_1$ =132 mV G[mV/fC]~500 RMS noise~4 mV ENC~50 e- $\mu_2$ =146 mV

The low noise allows disentangling the 2<sup>nd</sup> peak (5.90 e 6.49 keV far 164e-~3ENC)

# The "first" (Chip1) Gain with C<sub>ini</sub>=60 fF

(Set  $V_{fbk}$ = 320 mV  $\rightarrow$  waveform shape closer to simulation)

#### T5TC\_chip1\_M1



### Chip1: first hints of gain/noise dispersion...

(Set  $V_{fbk}$ = 320 mV  $\rightarrow$  waveform shape closer to simulation)



<ENC>= 36 e- σ(ENC)=15 e-

It's not surprising ... (apsel5T-ST)







# Sr-90 Spectrum (chip4)

- Trigger: sgn[2,2]>5 $\sigma_{[2,2]}$  within a 4µs window after the scintillator fires (100 kevts written).
- In the offline analysis, due to the T<sub>peak</sub> dependance on V<sub>out</sub><sup>max</sup>,not to biased by positive noise oscillation and to sum the contribution of the other pixels to the cluster charge, we can apply 2 methods:
- 1. look for the max. signal  $V_{max}[i,j]$  in a shorter time window  $\Delta T$ , request that  $V_{max}[2,2] > V_{max}[i,j]_{i!=2,j!=2}$ , find the  $T_{max[2,2]}$  and sum-up the other 8  $V_{max}[i,j]$  found within  $T_{max[2,2]}$



(CPU time  $\rightarrow$  pre-select events:  $V_{max}[2,2] > V_{max}[i,j]_{i!=2,j!=2}$ ) and then sum the fitted  $V_{max}[i,j]$  to give the cluster charge

### Sr-90 Spectrum (method-1)



The Source distribution contains true  $\beta$  (scintillator fired!) but not impinging on the matrix (the mechanical collimator lets them pass). To estimate them, the Normalized No-Source distribution is taken w/o source with a pulse at the average scintillator frequency, normalizing to the same DAQ time.

For M2: MPV= 39.3 mV > SGN=890e-

### Sr-90 Spectrum (method-2)



Hypothesis: all the channels of the matrix have the PA responding with a waveform-shape equal to that of the (injectable) central pixel.

For **M2**: MPV= 26.0 mV SGN=590e-

### Some notes ...

- The chip#4 is the best of a small (5 chips) production:
  - Chip 1: to be further investigated in PV (by Laser SCAN);
  - Chip 2: gain extremely low (PV)
  - Chip 3: M1-pixel[2,2] oscillates (RMS 12 mV)
  - Chip 5: M1:pixel[1,3] oscillates; 3 pixels of M2 are noisy.
- More stat. needed to judge quality and yield (assuming these single problems are not caused by u-bonding, almost "perfect" in the past productions).
- "A posteriori" (after closing the design) we realized that a shaper-less FE is not the most robust/performing design to test a new technology (apsel5T ST "docet").
- The main contribution of the Q-cluster comes from the central pixel (request that in order to analyze clusters well-contained in the 3x3 matrix).
- The Q-cluster now doesn't take into account the spread on the gain (sum the 9 output voltages instead of the 9 charges).
- To be confirmed the difference btw M1 and M2.
- The first 2 chips have been sent to PV to be tested under LASER scan.

## Conclusions

- First encouraging test results on the apsel structures of the V.I. chips:
  - The process produced a working sensor (at least) at analog level
  - The noise and gain are "reasonable"
  - The electrode collects a charge from MIP of about 700e-
- An un-biased estimate of the charge collected by the cluster to be done in the September Test-Beam (SPS), with a pure sample of MIP tracks (telescope used) impinging on the matrix



 The OK flag for the submission of the 1<sup>st</sup> T.C. run→ test the digital part in the 2 tiers assembly (...coming soon).